

d) Amendments to the Claims

Please cancel claims 2-4, 16-18 and 31-50 without prejudice or disclaimer.

Kindly amend claims 1, 8, 10, 12-15, 22 and 24-28 as follows. A detailed listing of all the claims is provided.

1. (Currently Amended) An exhaust processing method of exhausting a processing space for subjecting a substrate or a film to plasma processing, which comprises:

providing chemical-reaction inducing means in an exhaust line connecting the processing space to exhaust means;[[,]] and

causing chemical reaction of at least either an unreacted gas of a byproduct exhausted from the processing space to chemically react without allowing plasma in the processing space to reach the chemical-reaction inducing means,

wherein the chemical reaction of at least either the unreacted gas or the byproduct exhausted from the processing space is caused by heating of the chemical-reaction inducing means,

wherein a metal member is the chemical-reaction inducing means, and

wherein the metal member is at least one of chromium, molybdenum, tungsten, vanadium, niobium, tantalum, titanium, zirconium or hafnium.

2-4. (Cancelled)

5. (Original) The exhaust processing method according to claim 1, wherein means for blocking plasma is provided between the processing space and the chemical-reaction inducing means.

6. (Original) The exhaust processing method according to claim 5, wherein a conductive member is provided as the means for blocking plasma and has a potential different from that in a plasma space.

7. (Original) The exhaust processing method according to claim 6, wherein a metal member is used as the conductive member.

8. (Currently Amended) The exhaust processing method according to claim 6, wherein a material used for the chemical-reaction inducing means is ~~similarly~~ the same as used for the conductive member.

9. (Original) The exhaust processing method according to claim 5, wherein an electrically grounded member is used as the means for blocking plasma.

10. (Currently Amended) The exhaust processing method according to claim 5, wherein one or more linear members or ~~spirally wound linear members~~ a linear member formed by a spiral winding are used as the means for blocking plasma.

11. (Original) The exhaust processing method according to claim 5, wherein a mesh is used as the means for blocking plasma.

12. (Currently Amended) The exhaust processing method according to claim 5, wherein a ~~plate-like~~ plate-shaped member having a shape for preventing passage of the plasma is used as the means for blocking plasma.

13. (Currently Amended) The exhaust processing method according to claim 5, wherein a ~~plate-like~~ plate-shaped member with openings is used as the means for blocking plasma.

14. (Currently Amended) The exhaust processing method according to claim 5, wherein a ~~plate-like~~ plate-shaped member is used as the means for blocking plasma, and the ~~plate-like~~ plate-shaped member is arranged in the exhaust line so that a gap is provided between the ~~plate-like~~ plate-shaped member and an inner wall of the exhaust line.

15. (Currently Amended) A plasma processing method for subjecting a substrate or a film to plasma processing, which comprises:

arranging a chemical-reaction inducing means in an exhaust line connecting a processing space for plasma processing to exhaust means for exhausting the processing space;[[,]] and

causing chemical reaction of at least either an unreacted gas or byproduct exhausted from the processing space without allowing plasma in the processing space to reach the chemical-reaction inducing means,

wherein the chemical reaction of at least either the unreacted gas or byproduct exhausted from the processing space is caused by heating of the chemical-reaction inducing means,

wherein a metal member is the chemical-reaction inducing means, and

wherein the metal member is at least one of chromium, molybdenum, tungsten, vanadium, niobium, tantalum, titanium, zirconium or hafnium.

16-18. (Cancelled)

19. (Original) The plasma processing method according to claim 15, wherein means for blocking plasma is provided between the processing space and the chemical-reaction inducing means.

20. (Original) The plasma processing method according to claim 19, wherein a conductive member is provided as the means for blocking plasma and has a potential different from that in a plasma space.

21. (Original) The plasma processing method according to claim 20, wherein a metal member is used as the conductive member.

22. (Currently Amended) The plasma processing method according to claim 20, wherein a material used for the chemical-reaction inducing means is ~~similarly the~~ same as used for the conductive member.

23. (Original) The plasma processing method according to claim 19, wherein the means for blocking plasma comprises an electrically grounded member.

24. (Currently Amended) The plasma processing method according to claim 19, wherein one or more linear members or ~~spirally-wound linear members~~ a linear member formed by a spiral winding are used as the means for blocking plasma.

25. (Currently Amended) The plasma processing method according to claim 19, wherein a mesh is used as the means for blocking plasma.

26. (Currently Amended) The plasma processing method according to claim 19, wherein a ~~plate-like~~ plate-shaped member having a shape for preventing passage of the plasma is used as the means for blocking plasma

27. (Currently Amended) The plasma processing method according to claim 19, wherein a ~~plate-like~~ plate-shaped member with openings is used as the means for blocking plasma.

28. (Currently Amended) The plasma processing method according to claim 19, wherein a ~~plate-like~~ plate-shaped member is used as the means for blocking plasma, and the ~~plate-like~~ plate-shaped member is arranged in the exhaust line so that a gap is provided between the ~~plate-like~~ plate-shaped member and an inner wall of the exhaust line.

29. (Original) The plasma processing method according to claim 15, wherein the plasma processing is film formation conducted by a plasma CVD process.

30. (Original) The plasma processing method according to claim 15, wherein the plasma processing is plasma etching a substrate or a film.

31-50. (Cancelled)